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(54) **CAPACITOR AND SEMICONDUCTOR  
DEVICE INCLUDING THE CAPACITOR**

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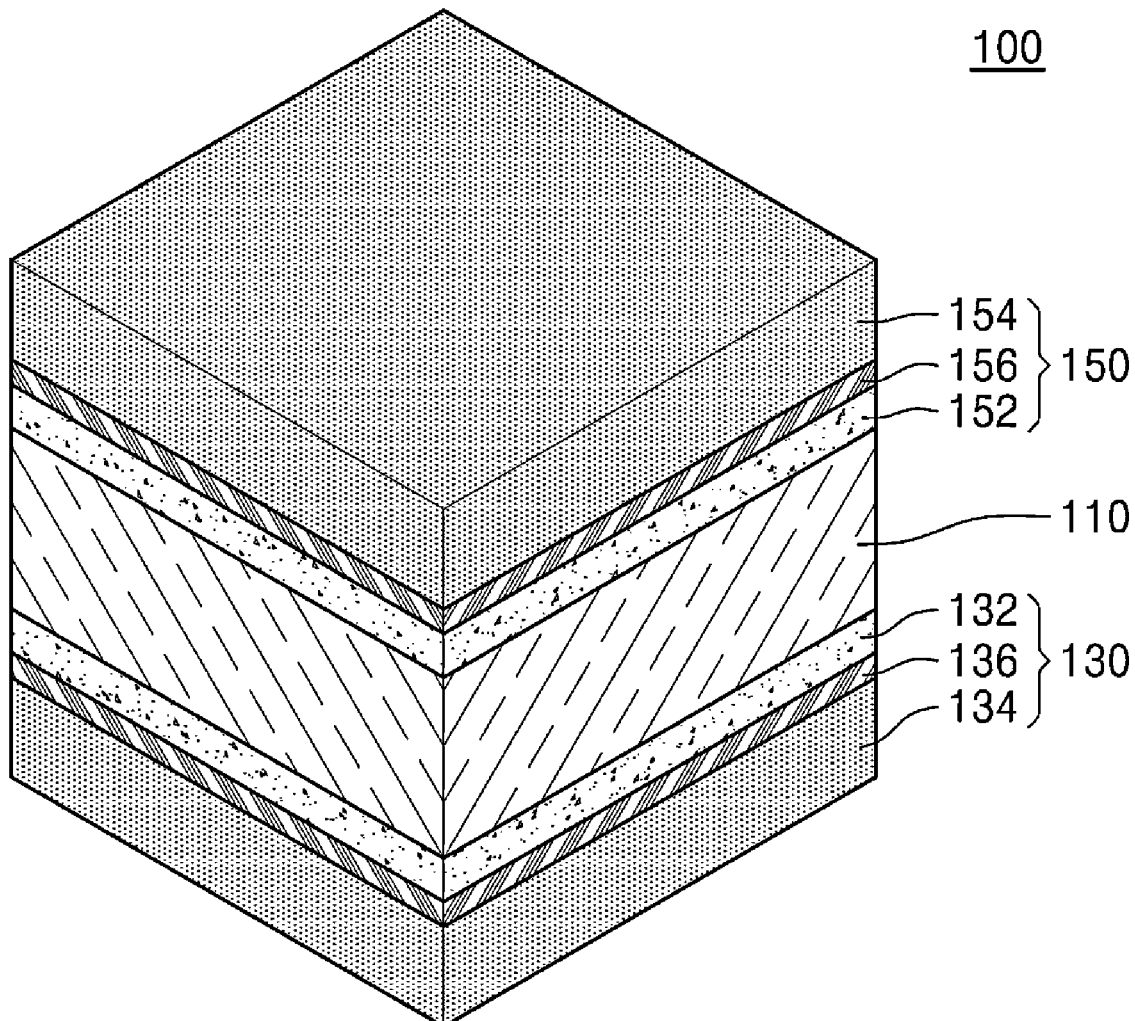
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**ABSTRACT**

Provided are a capacitor and a semiconductor device including the same. The capacitor includes: a dielectric layer having a perovskite crystal structure; and first and second electrodes spaced apart from each other with the dielectric layer therebetween. At least one of the first and second electrodes includes a metallic layer having a perovskite crystal structure, a first ionic layer having ionic properties, and a semiconductor layer.



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